## **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# **PDTC123E series** NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

Product data sheet Supersedes data of 2004 Mar 18 2004 Aug 06



# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

### **APPLICATIONS**

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
R1	bias resistor	2.2	_	kΩ
R2	bias resistor	2.2	_	kΩ

### **DESCRIPTION**

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACI	KAGE	MARKING CODE	DND COMPLEMENT	
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT	
PDTC123EE	SOT416	SC-75	5A	PDTA123EE	
PDTC123EEF	SOT490	SC-89	6A	PDTA123EEF	
PDTC123EK	SOT346	SC-59	48	PDTA123EK	
PDTC123EM	SOT883	SC-101	G1	PDTA123EM	
PDTC123ES	SOT54 (TO-92)	SC-43	TC123E	PDTA123ES	
PDTC123ET	SOT23	_	*26 <sup>(1)</sup>	PDTA123ET	
PDTC123EU	SOT323	SC-70	*48 <sup>(1)</sup>	PDTA123EU	

### Note

<sup>1. \* =</sup> p: Made in Hong Kong.

<sup>\* =</sup> t: Made in Malaysia.

<sup>\* =</sup> W: Made in China.

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

# PDTC123E series

# SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL	PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION	
PDTC123ES	2 R1 R2 3 MAM364	1 2 3	base collector emitter	
PDTC123EE PDTC123EEF PDTC123EK PDTC123ET PDTC123EU	Top view  1 R1 R2 R2 R2 R2 R2 RDB269	1 2 3	base emitter collector	
PDTC123EM	2 R1 R2 Dottom view MHC506	1 2 3	base emitter collector	

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

### **ORDERING INFORMATION**

TYPE NUMBER	PACKAGE							
ITPE NUMBER	NAME	NAME DESCRIPTION						
PDTC123EE	_	plastic surface mounted package; 3 leads	SOT416					
PDTC123EEF	_	plastic surface mounted package; 3 leads	SOT490					
PDTC123EK	_	plastic surface mounted package; 3 leads	SOT346					
PDTC123EM	-	leadless ultra small package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883					
PDTC123ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54					
PDTC123ET	_	plastic surface mounted package; 3 leads	SOT23					
PDTC123EU	_	plastic surface mounted package; 3 leads	SOT323					

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+12	V
	negative		_	-10	V
Io	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu m$  copper strip line.

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

### **Notes**

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu m$  copper strip line.

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A	_	_	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A	_	_	2	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 20 mA	30	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
$V_{i(off)}$	input-off voltage	I <sub>C</sub> = 1 mA; V <sub>CE</sub> = 5 V	_	1.2	0.5	V
V <sub>i(on)</sub>	input-on voltage	$I_C = 20 \text{ mA}; V_{CE} = 0.3 \text{ V}$	2	1.6	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	_	_	2.5	pF

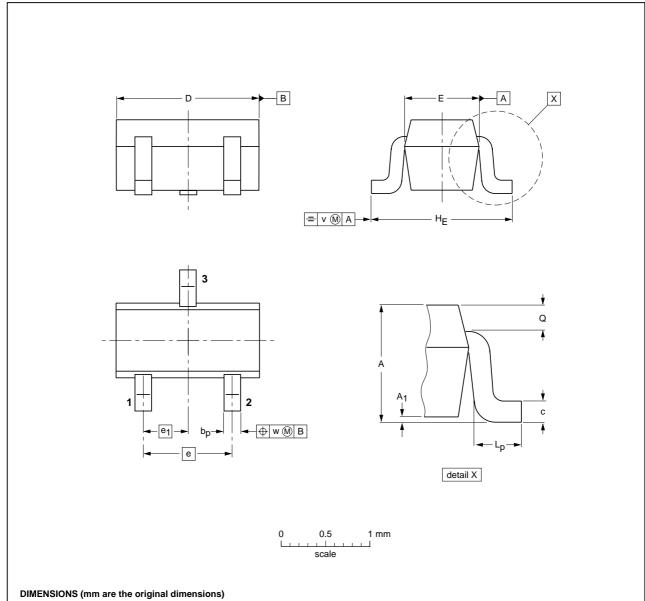
# NPN resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$ , $R2 = 2.2 \text{ k}\Omega$

## PDTC123E series

### **PACKAGE OUTLINES**

Plastic surface-mounted package; 3 leads

**SOT416** 



DIMENS	IONS (I	nm are	the origi	nai dim	ensions)	
						-

U	INIT	Α	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	ø	v	w
r	mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT416			SC-75		<del>-04-11-04</del> 06-03-16	

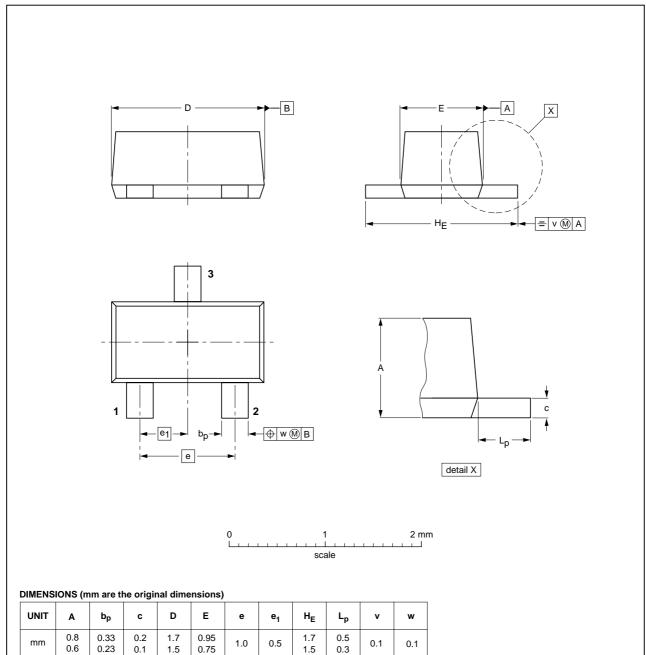
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# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Plastic surface-mounted package; 3 leads

SOT490



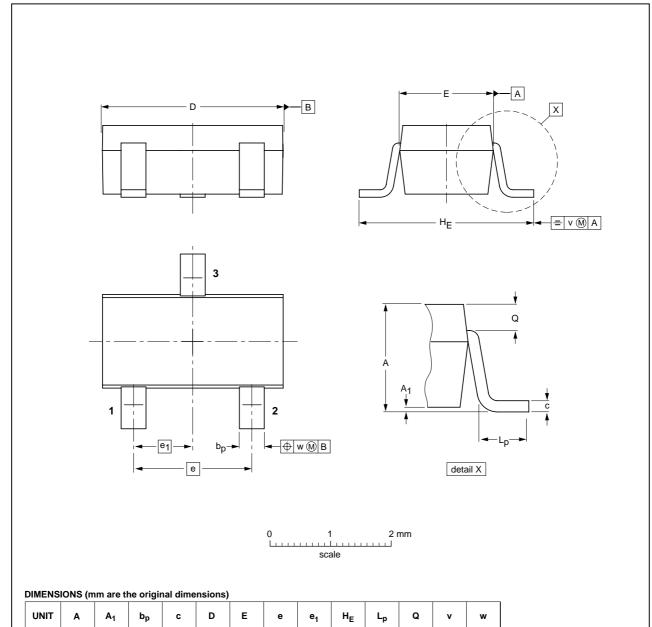
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT490			SC-89		<del>05-07-28</del> 06-03-16	

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Plastic surface-mounted package; 3 leads

**SOT346** 



OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1990E DATE	
SOT346		TO-236	SC-59A		<del>-04-11-11</del> 06-03-16	

1.9

0.6

0.33

0.2

2004 Aug 06 8

1.3

1.0

0.1

0.013

0.50

0.35

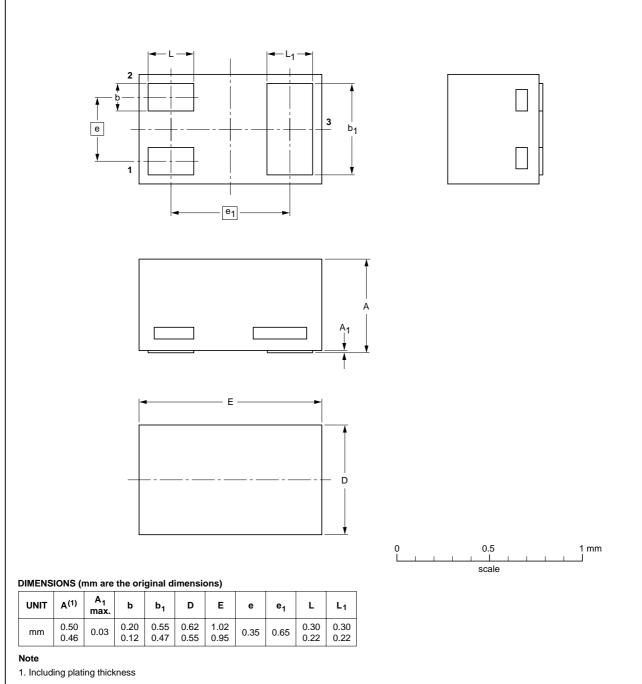
0.26

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

**SOT883** 



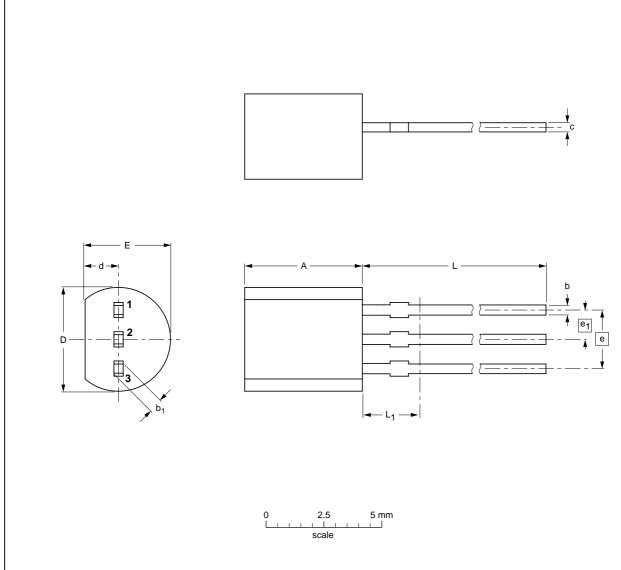
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			<del>03-02-05</del> 03-04-03

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Plastic single-ended leaded (through hole) package; 3 leads

SOT54



### **DIMENSIONS (mm are the original dimensions)**

UNIT	Α	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

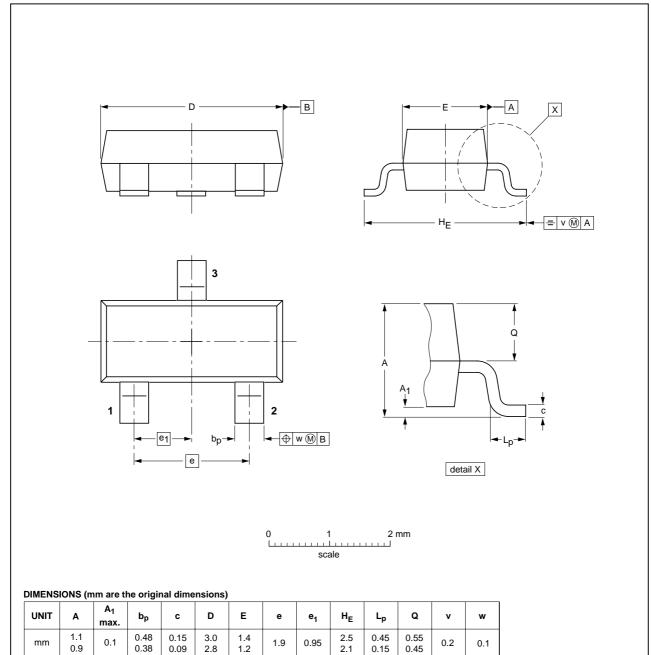
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			<del>04-06-28</del> 04-11-16

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Plastic surface-mounted package; 3 leads

SOT23



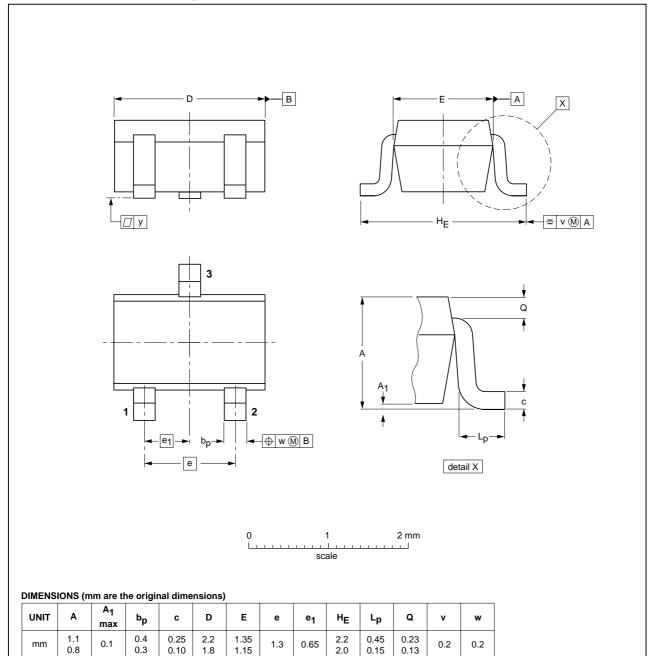
	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	TO-236AB				<del>-04-11-04</del> 06-03-16
-	IEC	IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

# NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

## Plastic surface-mounted package; 3 leads

**SOT323** 



OUTLINE		EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT323			SC-70			<del>04-11-04</del> 06-03-16	

## NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

## PDTC123E series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **NXP Semiconductors**

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com
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